TOSHIBA Transistor Silicon PNP Epitaxial Type

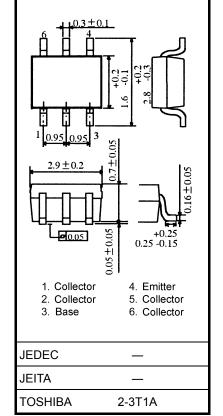
TPC6601

High-Speed Switching Applications DC-DC Converter Applications

- High DC current gain: $h_{FE} = 200$ to 500 (IC = -0.3 A)
- Low collector-emitter saturation voltage: V_{CE} (sat) = -0.2 V (max)
- High-speed switching: t_f = 90 ns (typ.)

Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Collector-base voltage		V _{CBO}	-50	V	
Collector-emitter voltage		V _{CEO}	-50	V	
Emitter-base voltage		V _{EBO}	-7	V	
Collector current	DC	Ι _C	-2.0	А	
	Pulse	I _{CP}	-3.5		
Base current		Ι _Β	-0.2	А	
Collector power dissipation	DC	P _C	0.8	W	
	t = 10 s	(Note 1)	1.6		
Junction temperature		Tj	150	°C	
Storage temperature range		T _{stg}	–55 to 150	°C	



Note 2: Using continuously under heavy loads (e.g. the application of

high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

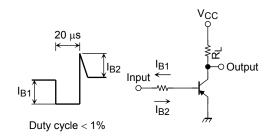
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Mounted on an FR4 board (glass epoxy, 1.6 mm thick, Cu area: 645 mm²)

Weight: 0.011 g (typ.)

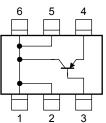
Electrical Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit	
Collector cut-off current		I _{CBO}	$V_{CB} = -50 \text{ V}, \text{ I}_{E} = 0$			-100	nA	
Emitter cut-off current		I _{EBO}	$V_{EB} = -7 V, I_C = 0$			-100	nA	
Collector-emitter breakdown voltage		V (BR) CEO	$I_{\rm C} = -10$ mA, $I_{\rm B} = 0$	-50	_	_	V	
DC current gain		h _{FE} (1)	$V_{CE} = -2 \text{ V}, \text{ I}_{C} = -0.3 \text{ A}$	200	_	500		
		h _{FE} (2)	$V_{CE} = -2 V, I_C = -1.0 A$	100	_	_		
Collector-emitter saturation voltage		V _{CE (sat)}	$I_{C} = -1.0 \text{ A}, I_{B} = -33 \text{ mA}$	_	_	-0.2	V	
Base-emitter saturation voltage		V _{BE (sat)}	$I_{C} = -1.0 \text{ A}, I_{B} = -33 \text{ mA}$	_	_	-1.1	V	
Switching time	Rise time	t _r	See Figure 1 circuit diagram.		60			
	Storage time	t _{stg}	$V_{CC} \simeq -30 \text{ V}, \text{ R}_{L} = 30 \Omega$		250		ns	
	Fall time	t _f	$I_{B1} = -I_{B2} = -33 \text{ mA}$		90			

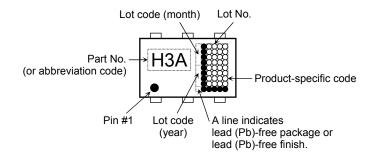




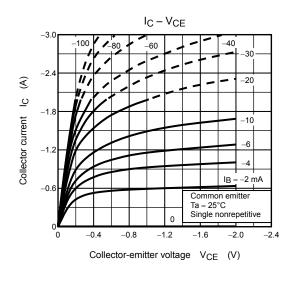
Circuit Configuration

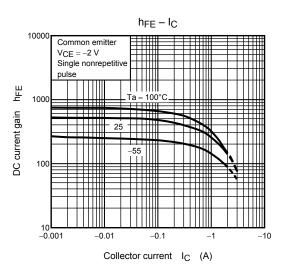


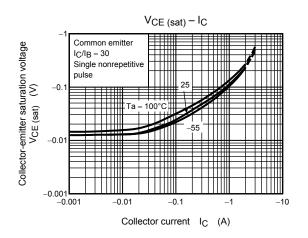
Marking

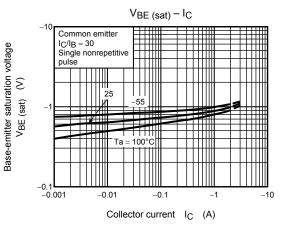


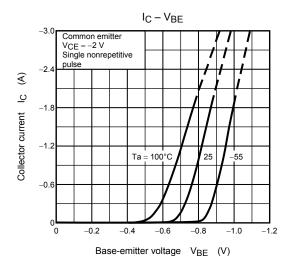
TOSHIBA

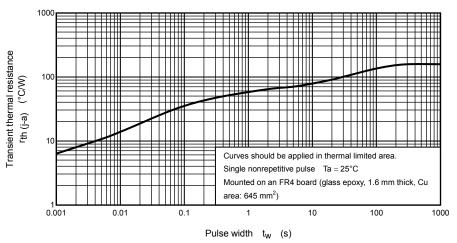




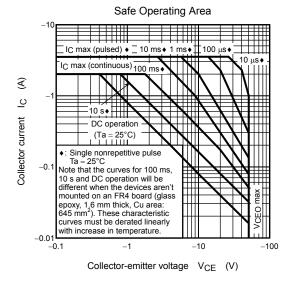








Transient Thermal Resistance rth - tw



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